NCV8130

300 mA, Very Low Dropout Bias Rail CMOS Voltage Regulator

The NCV8130 is a 300 mA VLDO equipped with NMOS pass transistor and a separate bias supply voltage (V_{BIAS}). The device provides very stable, accurate output voltage with low noise suitable for space constrained, noise sensitive applications. In order to optimize performance for battery operated portable applications, the NCV8130 features low I_Q consumption. The XDFN6 1.2 mm x 1.2 mm package is optimized for use in space constrained applications.

Features

- Input Voltage Range: 0.8 V to 5.5 V
- Bias Voltage Range: 2.4 V to 5.5 V
- Fixed Output Voltage Device
- Output Voltage Range: 0.8 V to 2.1 V
- ±1.5% Accuracy over Temperature, 0.5% V_{OUT} @ 25°C
- Ultra−Low Dropout: 150 mV Maximum at 300 mA
- Very Low Bias Input Current of Typ. 80 μA
- Very Low Bias Input Current in Disable Mode: Typ. 0.5 μA
- Logic Level Enable Input for ON/OFF Control
- Output Active Discharge Option Available
- Stable with a 1 μF Ceramic Capacitor
- NCV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC−Q100 Qualified and PPAP Capable; Device Temperature Grade 1: −40°C to +125°C Ambient Operating Temperature Range
- These are Pb−Free Devices

Typical Applications

- Automotive, Consumer and Industrial Equipment Point of Load Regulation
- Battery−powered Equipment
- FPGA, DSP and Logic Power Supplies
- Switching Power Supply Post Regulation
- Cameras, DVRs, STB and Camcorders

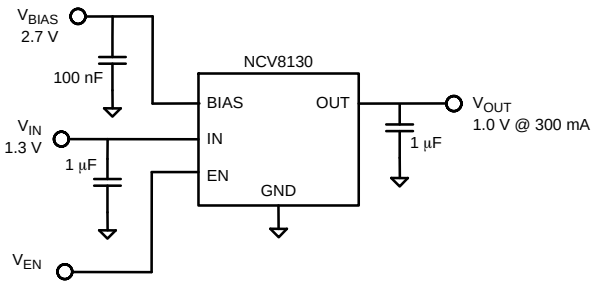

Figure 1. Typical Application Schematics

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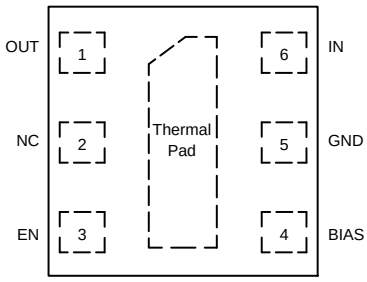
MARKING DIAGRAM

XDFN6
CASE 711AT

XX = Specific Device Code
M = Date Code

PIN CONNECTIONS



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ORDERING INFORMATION

See detailed ordering, marking and shipping information on page 9 of this data sheet.

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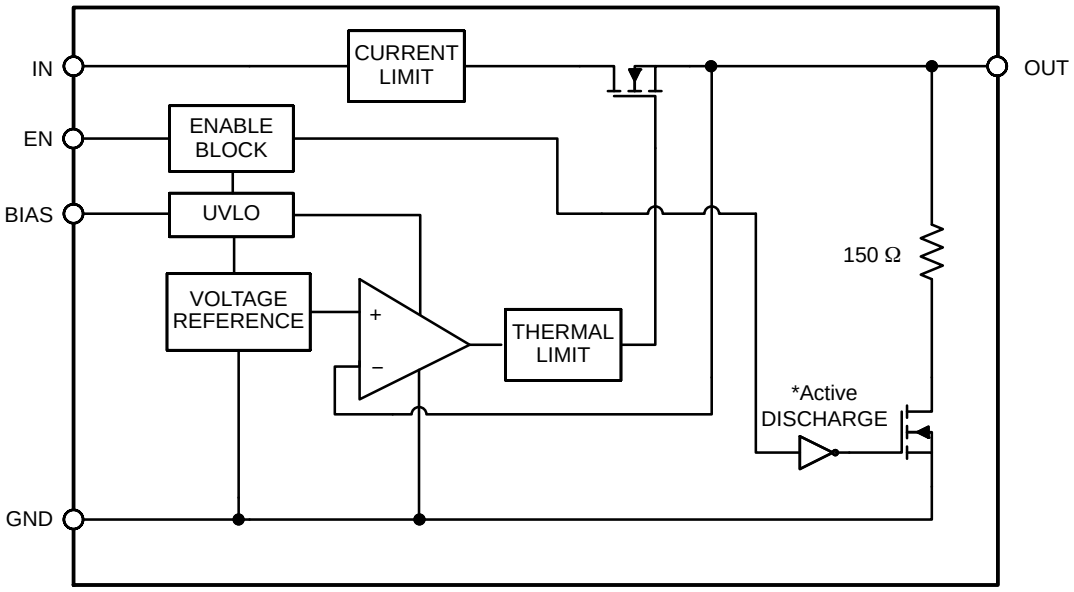


*Active output discharge function is present only in NCV8130AMXyyyTCG devices.
yyy denotes the particular output voltage option.

Figure 2. Simplified Schematic Block Diagram

PIN FUNCTION DESCRIPTION

Pin No.	Pin Name	Description
1	OUT	Regulated Output Voltage pin
2	N/C	Not internally connected (Note 1)
3	EN	Enable pin. Driving this pin high enables the regulator. Driving this pin low puts the regulator into shutdown mode.
4	BIAS	Bias voltage supply for internal control circuits. This pin is monitored by internal Under-Voltage Lockout Circuit.
5	GND	Ground pin
6	IN	Input Voltage Supply pin
Pad		Should be soldered to the ground plane for increased thermal performance.

1. True no connect. Printed circuit board traces are allowable

ABSOLUTE MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Input Voltage (Note 2)	V_{IN}	−0.3 to 6	V
Output Voltage	V_{OUT}	−0.3 to (V_{IN}+0.3) ≤ 6	V
Chip Enable and Bias Input	V_{EN}, V_{BIAS}	−0.3 to 6	V
Output Short Circuit Duration	t_{SC}	unlimited	s
Maximum Junction Temperature	T_J	150	°C
Storage Temperature	T_{STG}	−55 to 150	°C
ESD Capability, Human Body Model (Note 3)	ESD_{HBM}	2000	V
ESD Capability, Machine Model (Note 3)	ESD_{MM}	200	V

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

2. Refer to ELECTRICAL CHARACTERISTICS and APPLICATION INFORMATION for Safe Operating Area.
3. This device series incorporates ESD protection (except OUT pin) and is tested by the following methods:
   ESD Human Body Model tested per AEC−Q100−002
   ESD Machine Model tested per AEC−Q100−003
   Latchup Current Maximum Rating ≤ 150 mA per AEC−Q100−004.

RECOMMENDED OPERATING CONDITIONS

Rating	Symbol	Min	Max	Unit
Input Voltage	V_{IN}	(V_{OUT} + V_{DO_IN})	5.5	V
Bias Voltage	V_{BIAS}	(V_{OUT} + 1.35) ≥ 2.4	5.5	V
Junction Temperature	T_J	−40	+125	°C

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

THERMAL CHARACTERISTICS

Rating	Symbol	Value	Unit
Thermal Characteristics, XDFN6 1.2 mm x 1.2 mm Thermal Resistance, Junction−to−Air	$R_{\theta JA}$	170	°C/W

ELECTRICAL CHARACTERISTICS

$-40°C \le T_J \le 125°C$; V_{BIAS} = 2.7 V or (V_{OUT} + 1.6 V), whichever is greater, $V_{IN} = V_{OUT(NOM)}$ + 0.3 V, I_{OUT} = 1 mA, V_{EN} = 1 V, unless otherwise noted. C_{IN} = 1 μF, C_{BIAS} = 0.1 μF, C_{OUT} = 1 μF (effective capacitance) (Note 4). Typical values are at T_J = +25°C. Min/Max values are for $-40°C \le T_J \le 125°C$ unless otherwise noted. (Note 5)

Parameter	Test Conditions	Symbol	Min	Typ	Max	Unit
Operating Input Voltage Range		V_{IN}	$V_{OUT}+V_{DO}$		5.5	V
Operating Bias Voltage Range		V_{BIAS}	(V_{OUT}+1.35) ≥2.4		5.5	V
Undervoltage Lock−out	V_{BIAS} Rising Hysteresis	UVLO		1.6 0.2		V
Output Voltage Accuracy	$-40°C \le T_J \le 125°C$, $V_{OUT(NOM)}$ + 0.3 V ≤ V_{IN} ≤ 5.0 V, 2.7 V or ($V_{OUT(NOM)}$ + 1.6 V), whichever is greater < V_{BIAS} < 5.5 V, 1 mA < I_{OUT} < 300 mA	V_{OUT}	−1.5		+1.5	%
Output Voltage Accuracy		V_{OUT}		±0.5		%
V_{IN} Line Regulation	$V_{OUT(NOM)}$ + 0.3 V ≤ V_{IN} ≤ 5.0 V	$Line_{Reg}$		0.01		%/V
V_{BIAS} Line Regulation	2.7 V or ($V_{OUT(NOM)}$ + 1.6 V), whichever is greater < V_{BIAS} < 5.5 V	$Line_{Reg}$		0.01		%/V
Load Regulation	I_{OUT} = 1 mA to 300 mA	$Load_{Reg}$		1.5		mV
V_{IN} Dropout Voltage	I_{OUT} = 300 mA (Note 6)	V_{DO}		75	175	mV
V_{BIAS} Dropout Voltage	I_{OUT} = 300 mA, $V_{IN} = V_{BIAS}$ (Notes 6, 7)	V_{DO}		1.1	1.4	V
Output Current Limit	V_{OUT} = 90% $V_{OUT(NOM)}$	I_{CL}	400	550	950	mA
Bias Pin Operating Current	V_{BIAS} = 2.7 V	I_{BIAS}		80	110	μA
Bias Pin Disable Current	V_{EN} ≤ 0.4 V	$I_{BIAS(DIS)}$		0.5	1.5	μA
Vinput Pin Disable Current	V_{EN} ≤ 0.4 V	$I_{VIN(DIS)}$		0.5	1.5	μA
EN Pin Threshold Voltage	EN Input Voltage “H”	$V_{EN(H)}$	0.9			V
	EN Input Voltage “L”	$V_{EN(L)}$			0.4	
EN Pull Down Current	V_{EN} = 5.5 V	I_{EN}		0.3	1.5	μA
Turn−On Time	C_{OUT} = 1 μF, From assertion of V_{EN} to V_{OUT} = 98% $V_{OUT(NOM)}$, $V_{OUT(NOM)}$ = 1.0 V	t_{ON}		150		μs
Power Supply Rejection Ratio	V_{IN} to V_{OUT}, f = 1 kHz, I_{OUT} = 300 mA, $V_{IN} \ge V_{OUT}$ +0.5 V	PSRR(V_{IN})		65		dB
	V_{BIAS} to V_{OUT}, f = 1 kHz, I_{OUT} = 300 mA, $V_{IN} \ge V_{OUT}$ +0.5 V	PSRR(V_{BIAS})		80		dB
Output Noise Voltage	$V_{IN} = V_{OUT}$ +0.5 V, $V_{OUT(NOM)}$ = 1.0 V, f = 10 Hz to 100 kHz	V_N		40		μV_{RMS}
Thermal Shutdown Threshold	Temperature increasing			160		°C
	Temperature decreasing			140		
Output Discharge Pull−Down	V_{EN} ≤ 0.4 V, V_{OUT} = 0.5 V, NCV8130A options only	R_{DISCH}		150		Ω

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Effective capacitance, including the effect of DC bias, tolerance and temperature. See the Application Information section for more information.
5. Performance guaranteed over the indicated operating temperature range by design and/or characterization. Production tested at T_A = 25°C. Low duty cycle pulse techniques are used during the testing to maintain the junction temperature as close to ambient as possible.
6. Dropout voltage is characterized when V_{OUT} falls 3% below $V_{OUT(NOM)}$.
7. For output voltages below 0.9 V, V_{BIAS} dropout voltage does not apply due to a minimum Bias operating voltage of 2.4 V.

APPLICATIONS INFORMATION

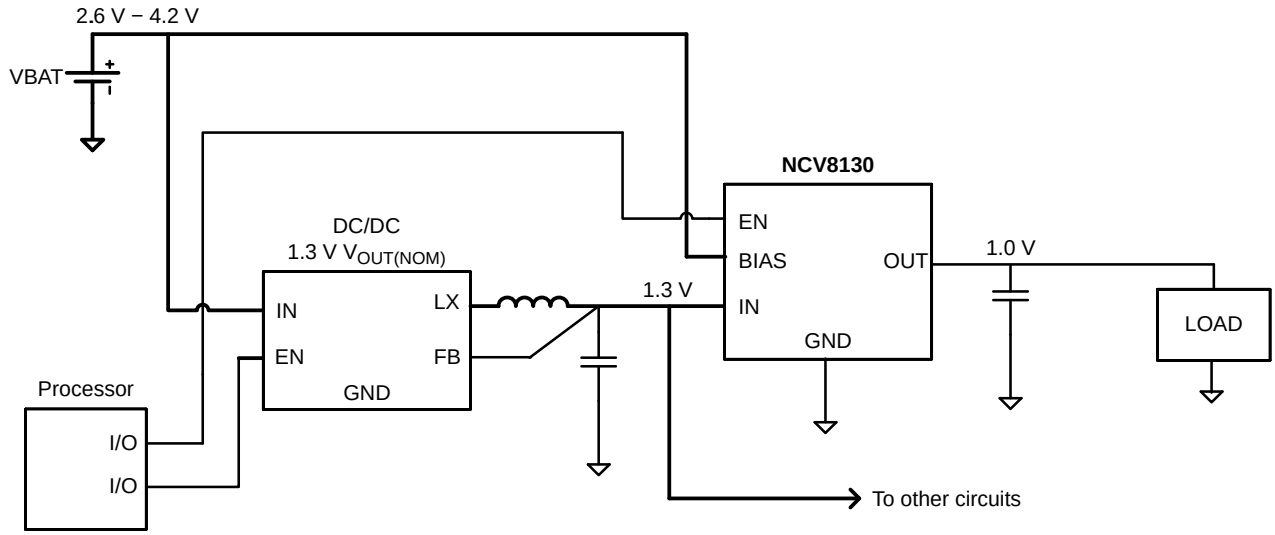


Figure 3. Typical Application: Low−Voltage Post−Regulator with ON/OFF functionality

TYPICAL CHARACTERISTICS

At T_J = +25°C, V_{IN} = $V_{OUT(TYP)}$ + 0.3 V, V_{BIAS} = 2.7 V, V_{EN} = V_{BIAS}, $V_{OUT(NOM)}$ = 1.0 V, I_{OUT} = 300 mA, C_{IN} = 1 μF, C_{BIAS} = 0.1 μF, and C_{OUT} = 1 μF (effective capacitance), unless otherwise noted.

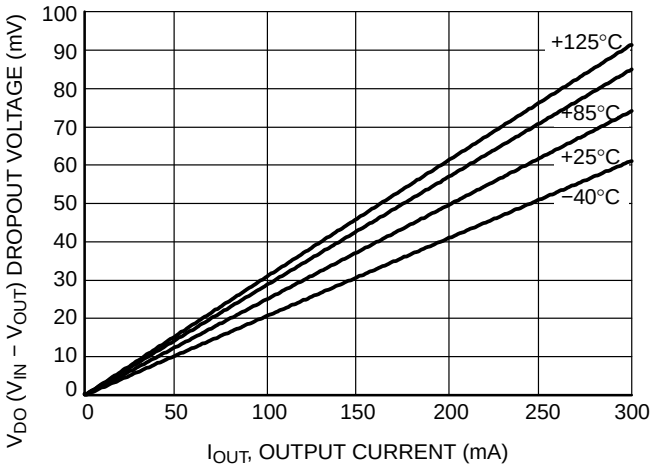


Figure 4. V_{IN} Dropout Voltage vs. I_{OUT} and Temperature T_J

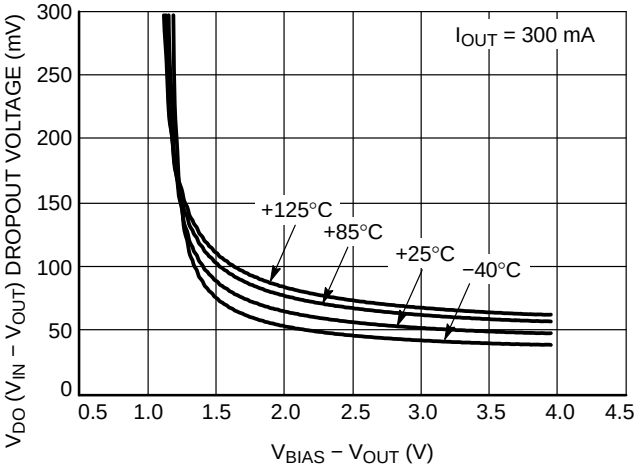


Figure 5. V_{IN} Dropout Voltage vs. (V_{BIAS} − V_{OUT}) and Temperature T_J

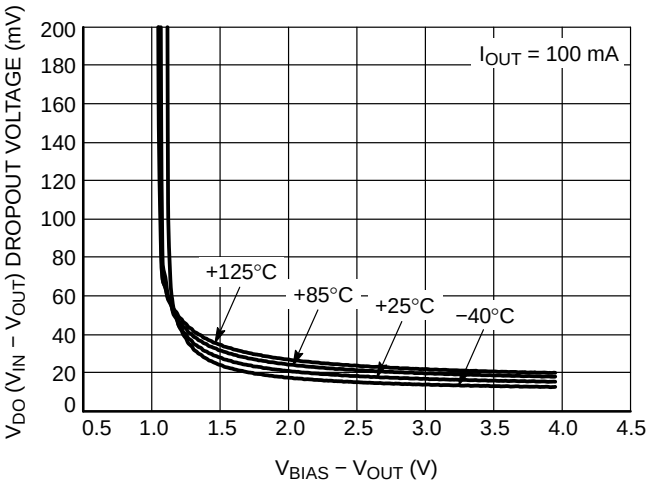


Figure 6. V_{IN} Dropout Voltage vs. (V_{BIAS} − V_{OUT}) and Temperature T_J

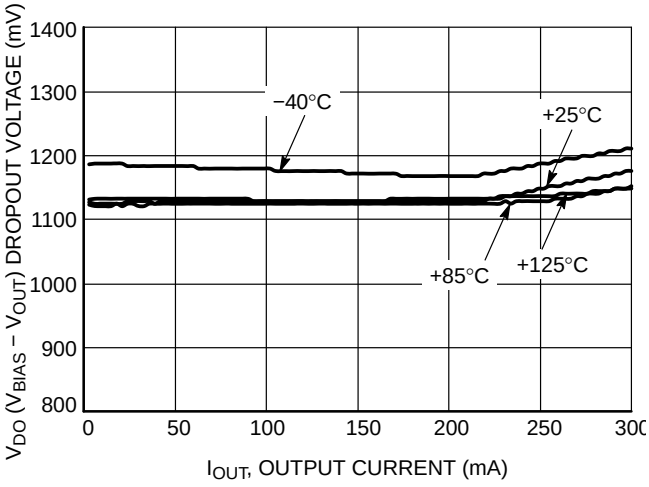


Figure 7. V_{BIAS} Dropout Voltage vs. I_{OUT} and Temperature T_J

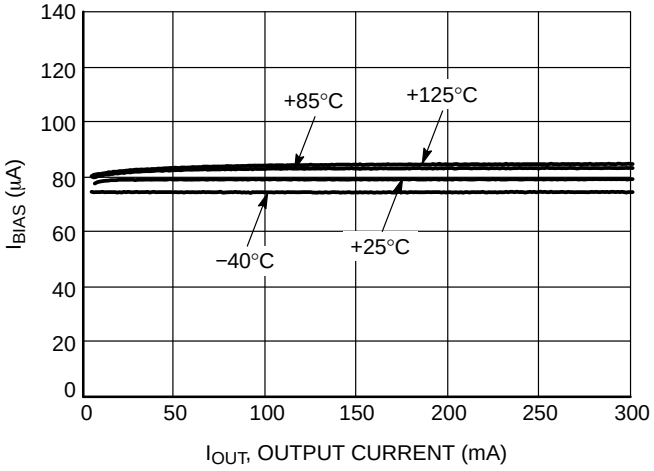


Figure 8. BIAS Pin Current vs. I_{OUT} and Temperature T_J

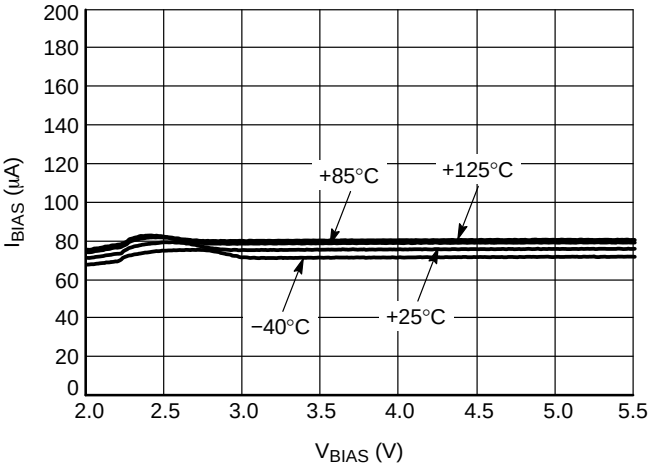


Figure 9. BIAS Pin Current vs. V_{BIAS} and Temperature T_J

TYPICAL CHARACTERISTICS

At T_J = +25°C, V_{IN} = $V_{OUT(TYP)}$ + 0.3 V, V_{BIAS} = 2.7 V, V_{EN} = V_{BIAS}, $V_{OUT(NOM)}$ = 1.0 V, I_{OUT} = 300 mA, C_{IN} = 1 μF, C_{BIAS} = 0.1 μF, and C_{OUT} = 1 μF (effective capacitance), unless otherwise noted.

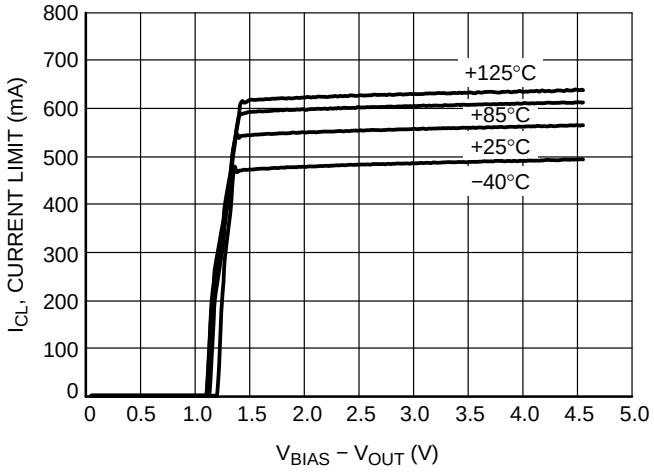


Figure 10. Current Limit vs. (V_{BIAS} − V_{OUT})

APPLICATIONS INFORMATION

The NCV8130 dual−rail very low dropout voltage regulator is using NMOS pass transistor for output voltage regulation from V_{IN} voltage. All the low current internal controll circuitry is powered from the V_{BIAS} voltage.

The use of an NMOS pass transistor offers several advantages in applications. Unlike a PMOS topology devices, the output capacitor has reduced impact on loop stability. V_{IN} to V_{OUT} operating voltage difference can be very low compared with standard PMOS regulators in very low V_{IN} applications.

The NCV8130 offers smooth monotonic start-up. The controlled voltage rising limits the inrush current.

The Enable (EN) input is equipped with internal hysteresis.

NCV8130 is a Fixed Voltage linear regulator.

Dropout Voltage

Because of two power supply inputs V_{IN} and V_{BIAS} and one V_{OUT} regulator output, there are two Dropout voltages specified.

The first, the V_{IN} Dropout voltage is the voltage difference ($V_{IN} - V_{OUT}$) when V_{OUT} starts to decrease by percents specified in the Electrical Characteristics table. V_{BIAS} is high enough, specific value is published in the Electrical Characteristics table.

The second, V_{BIAS} dropout voltage is the voltage difference ($V_{BIAS} - V_{OUT}$) when V_{IN} and V_{BIAS} pins are joined together and V_{OUT} starts to decrease.

Input and Output Capacitors

The device is designed to be stable for ceramic output capacitors with Effective capacitance in the range from 1 μF to 10 μF. The device is also stable with multiple capacitors in parallel, having the total effective capacitance in the specified range.

In applications where no low input supplies impedance available (PCB inductance in V_{IN} and/or V_{BIAS} inputs as example), the recommended C_{IN} = 1 μF and C_{BIAS} = 0.1 μF or greater. Ceramic capacitors are recommended**.** For the best performance all the capacitors should be connected to the NCV8130 respective pins directly in the device PCB copper layer, not through vias having not negligible impedance.

When using small ceramic capacitor, their capacitance is not constant but varies with applied DC biasing voltage, temperature and tolerance. The effective capacitance can be much lower than their nominal capacitance value, most importantly in negative temperatures and higher LDO output voltages. That is why the recommended Output capacitor capacitance value is specified as Effective value in the specific application conditions.

Enable Operation

The enable pin will turn the regulator on or off. The threshold limits are covered in the electrical characteristics table in this data sheet. If the enable function is not to be used then the pin should be connected to V_{IN} or V_{BIAS}.

Current Limitation

The internal Current Limitation circuitry allows the device to supply the full nominal current and surges but protects the device against Current Overload or Short.

Thermal Protection

Internal thermal shutdown (TSD) circuitry is provided to protect the integrated circuit in the event that the maximum junction temperature is exceeded. When TSD activated , the regulator output turns off. When cooling down under the low temperature threshold, device output is activated again. This TSD feature is provided to prevent failures from accidental overheating.

Power Dissipation

The maximum power dissipation supported by the device is dependent upon board design and layout. Mounting pad configuration on the PCB, the board material, and the ambient temperature affect the rate of junction temperature rise for the part. For reliable operation, junction temperature should be limited to +125°C.

ORDERING INFORMATION

Device	Nominal Output Voltage	Marking	Option	Package	Shipping†
NCV8130BMX080TCG	0.80 V	NL	Non−Active Discharge	XDFN6 (Pb−Free)	3000 / Tape & Reel
NCV8130BMX100TCG	1.00 V	NF			
NCV8130BMX110TCG	1.10 V	NG			
NCV8130BMX120TCG	1.20 V	NA			
NCV8130BMX130TCG	1.30 V	NC			
NCV8130BMX150TCG	1.50 V	ND			
NCV8130BMX180TCG	1.80 V	NE			

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

To order other package and voltage variants, please contact your ON sales representative.

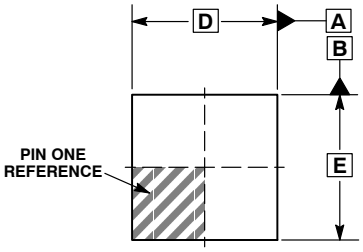
MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS

ON Semiconductor®

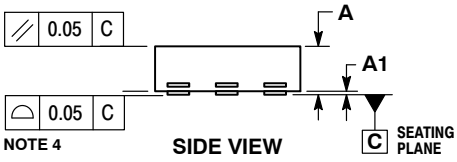
XDFN6 1.20x1.20, 0.40P
CASE 711AT
ISSUE C

SCALE 4:1

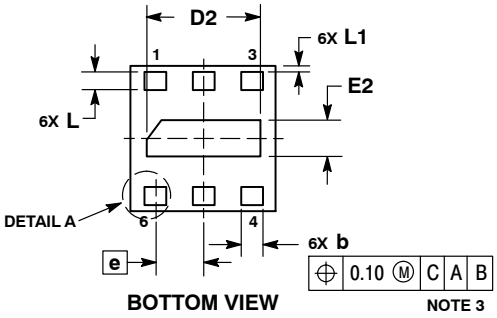
DATE 04 DEC 2015



TOP VIEW

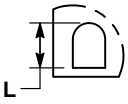


SIDE VIEW



BOTTOM VIEW

NOTE 3



DETAIL A
OPTIONAL CONSTRUCTION

NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION b APPLIES TO THE PLATED TERMINALS.
4. COPLANARITY APPLIES TO THE PAD AS WELL AS THE TERMINALS.

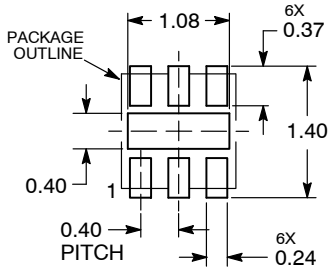
	MILLIMETERS		
DIM	MIN	TYP	MAX
A	0.30	0.37	0.45
A1	0.00	0.03	0.05
b	0.13	0.18	0.23
D	1.15	1.20	1.25
D2	0.84	0.94	1.04
E	1.15	1.20	1.25
E2	0.20	0.30	0.40
e	0.40 BSC		
L	0.15	0.20	0.25
L1	0.00	0.05	0.10

GENERIC MARKING DIAGRAM*

XX = Specific Device Code
M = Date Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “▪”, may or may not be present.

RECOMMENDED MOUNTING FOOTPRINT*



DIMENSIONS: MILLIMETERS

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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DESCRIPTION:	**XDFN6, 1.20 X 1.20, 0.40P**	**PAGE 1 OF 1**

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